



AMENDMENTS TO THE CLAIMS

B-1 subC-1

1. (Currently Amended) A semiconductor device, comprising:

- a first metallization layer;
- a first diffusion barrier layer disposed over said first metallization layer;
- a first etch stop layer disposed over and spaced from said first diffusion barrier layer;
- a dielectric layer disposed over said second etch stop layer;
- a via extending through said dielectric layer, said first etch stop layer, and said first diffusion barrier layer; and
- a sidewall diffusion barrier layer disposed on sidewalls of said via, said sidewall diffusion barrier layer formed by reverse sputtering of said first diffusion barrier layer, wherein said sidewall first diffusion barrier layer and said sidewall diffusion barrier layer are formed from a same material.

Claim 2 (Cancelled)

3. (Previously Amended) The semiconductor device according to claim 4, wherein said second etch stop layer includes silicon oxide

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4. (Currently Amended) A semiconductor device, comprising:

- a first metallization layer;
- a first diffusion barrier layer disposed over said first metallization layer;
- a second etch stop layer disposed on and contacting said first metallization diffusion layer;
- a first etch stop layer disposed on and contacting said second etch stop layer;

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a dielectric layer disposed on and contacting said first etch stop layer;
a via extending through said dielectric layer, said first etch stop layer, said second etch stop layer and said first diffusion barrier layer, wherein said second etch stop layer has a thickness of at least 50 angstroms to about 120 angstroms.

Claims 5 (Cancelled)

Claim 6 (Cancelled)

7. (Previously Amended) The semiconductor device according to claim 1, wherein said material of said first diffusion barrier layer includes silicon nitride.

8. (Original) The semiconductor device according to claim 7, wherein said first diffusion barrier layer has a thickness of at least 50 angstroms.

9. (Previously Amended) The semiconductor device according to claim 1, further comprising a second diffusion barrier layer disposed over said sidewall diffusion barrier layer.

10. (Original) The semiconductor device according to claim 1, wherein said dielectric layer includes silicon oxide.

11. (Original) The semiconductor device according to claim 10, wherein said metallization layer includes copper.

12. (Original) The semiconductor device according to claim 10, further comprising a conductive plug disposed within said via, and wherein said conductive plug includes copper.

13. (Original) The semiconductor device according to claim 1, wherein the via has rounded corners

Claims 14-18 (Cancelled)

Claims 19-30 (Withdrawn)